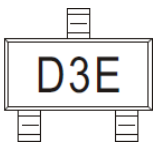
# RB411D SCHOTTKY BARRIER DIODE

SOT-23-3

## FEATURES

- Small Surface Mounting Type
- Low Reverse Current and Low Forward Voltage
- High Reliability

**Marking: D3E**



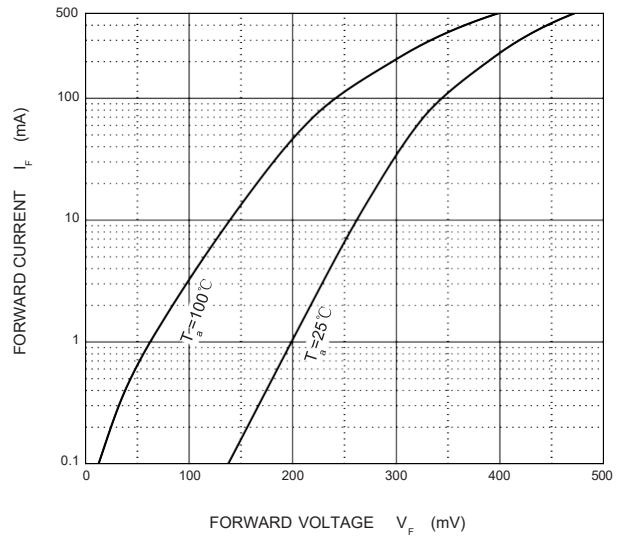

## Maximum Ratings(Ta=25℃ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|---|---|---|
| Peak repetitive reverse voltage | $V_{RM}$ | 40 | V |
| RMS reverse voltage | $V_{R(RMS)}$ | 28 | V |
| DC reverse voltage | $V_R$ | 20 | V |
| Mean rectifying output current | $I_O$ | 500 | mA |
| Forward Surge Current@t=8.3msNon-repetitivePeak | $I_{FSM}$ | 3 | A |
| Power Dissipation | $P_D$ | 200 | mW |
| Thermal Resistance Junction to Ambient | $R_{\theta JA}$ | 500 | ℃/W |
| Operating Junction Temperature Range | $T_j$ | -40 ~ +125 | ℃ |
| Storage Temperature Range | $T_{stg}$ | -55 ~ +150 | ℃ |

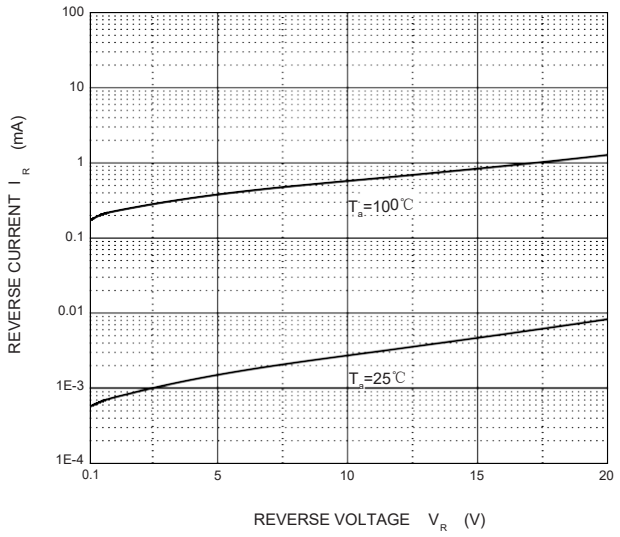
## Electrical Ratings @Ta=25℃

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Condition |
|---|---|---|---|---|---|---|
| Reverse breakdown voltage | $V_R$ | 20 | | | V | $I_R$=100μA |
| Forward voltage | $V_{F1}$ | | | 0.3 | V | $I_F$=10mA |
| | $V_{F2}$ | | | 0.5 | V | $I_F$=500mA |
| Reverse current | $I_R$ | | | 30 | μA | $V_R$=10V |
| Capacitance between terminals | $C_T$ | | 20 | | pF | $V_R$=10V,f=1MHz |

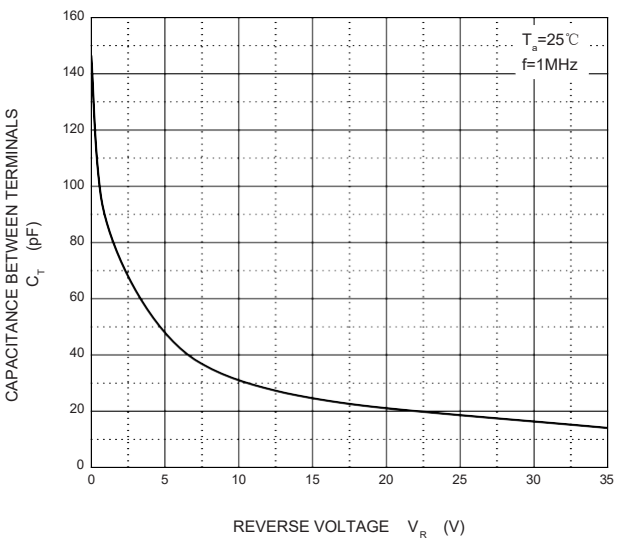
**Forward Characteristics**




**Reverse Characteristics**




**Capacitance Characteristics**




**Power Derating Curve**